



August 1998

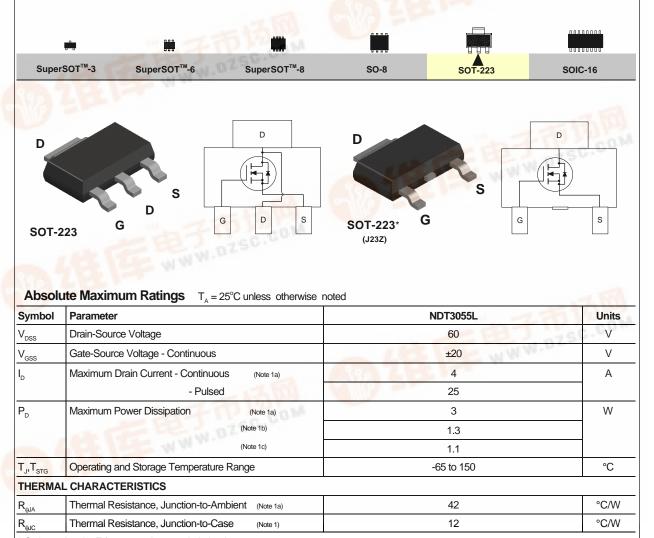
NDT3055L N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These logic level N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance, and withstand high energy pulse in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

Features

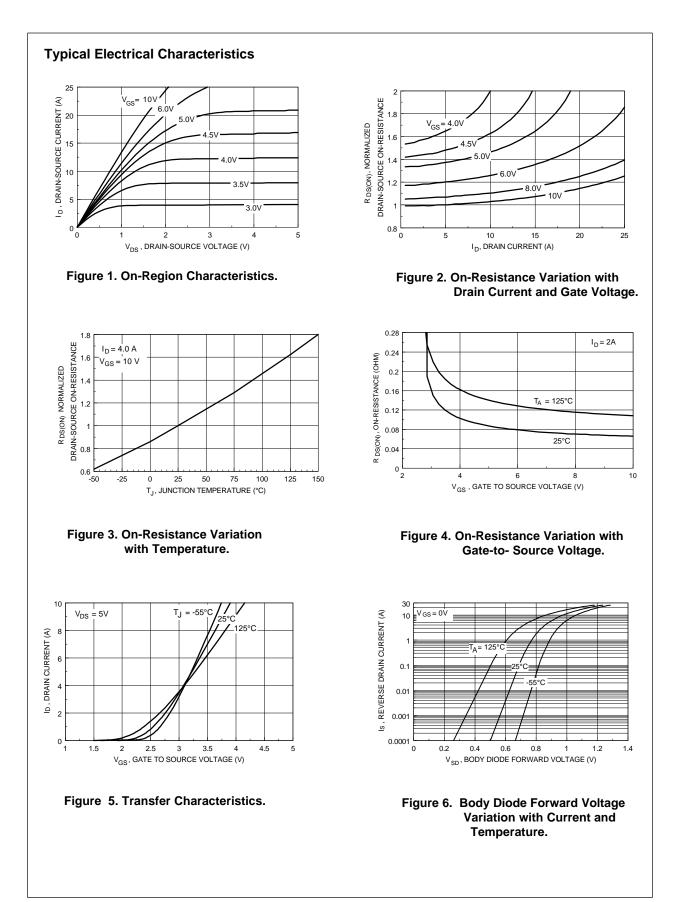
- $\label{eq:alpha} \begin{array}{l} \bullet \ \ \, \mbox{4 A, 60 V. R}_{\rm DS(ON)} = 0.100 \ \Omega \ @ \ \mbox{V}_{\rm GS} = 10 \ \mbox{V}, \\ R_{\rm DS(ON)} = 0.120 \ \Omega \ @ \ \mbox{V}_{\rm GS} = 4.5 \ \mbox{V}. \end{array}$
- Low drive requirements allowing operation directly from logic drivers. V_{GS(TH)} < 2V.
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.

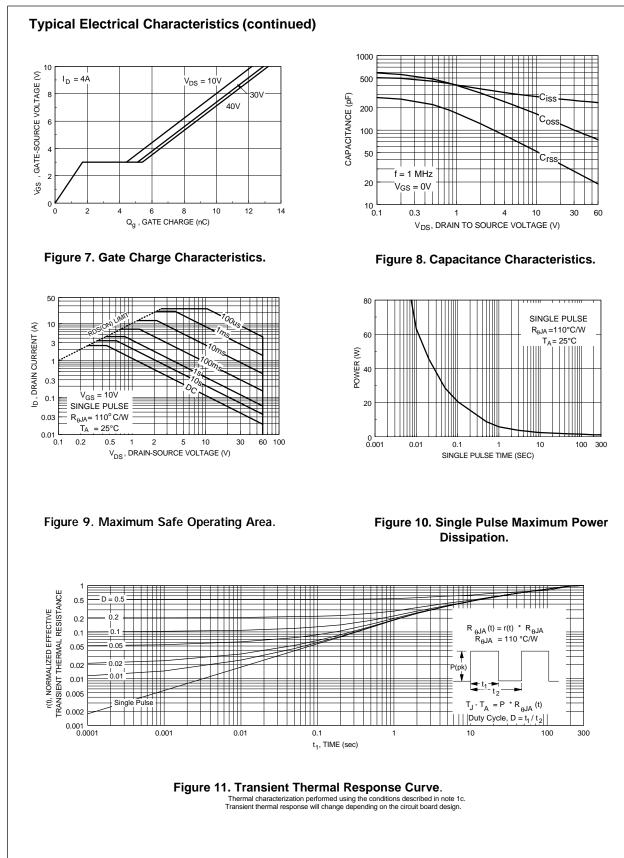


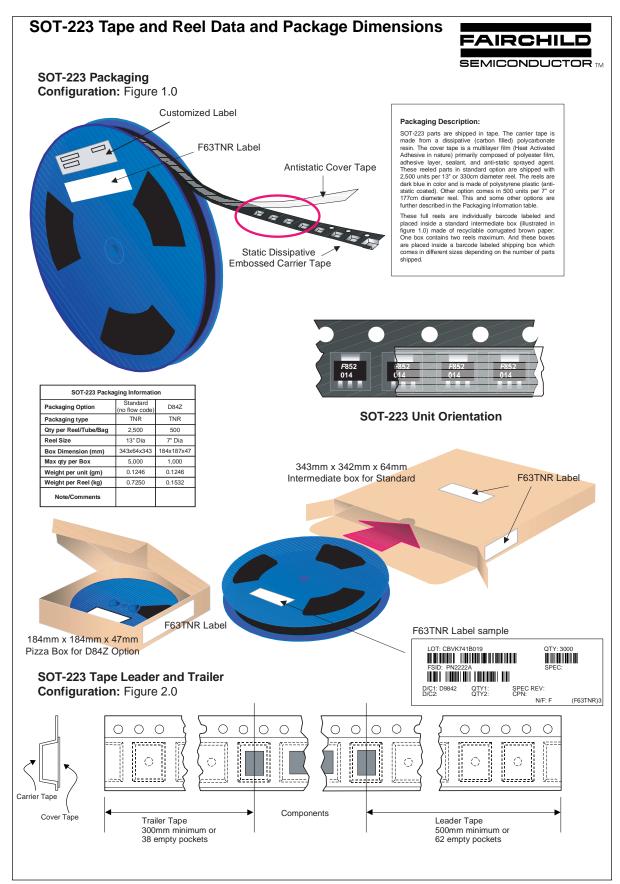
* Order option J23Z for cropped center drain lead.

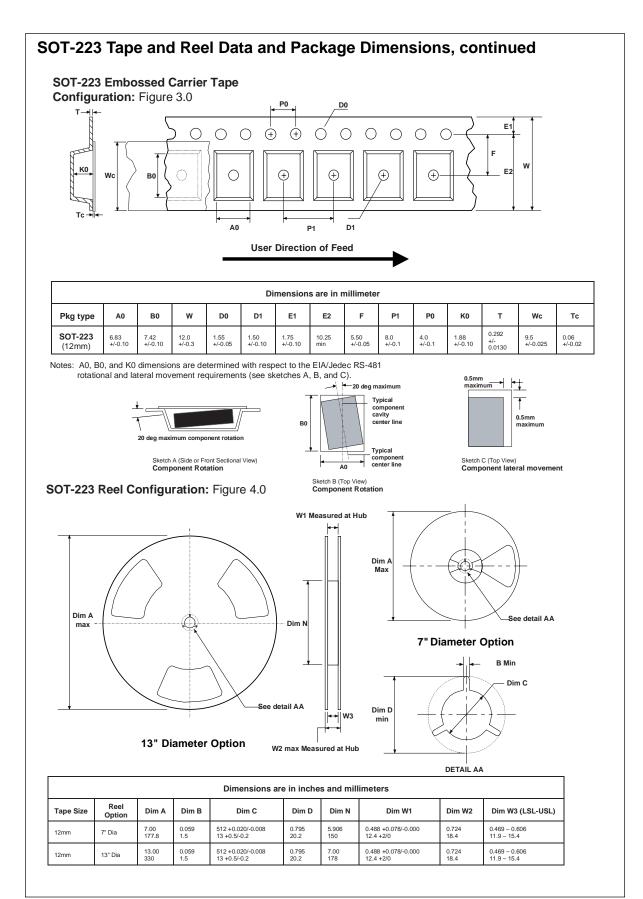
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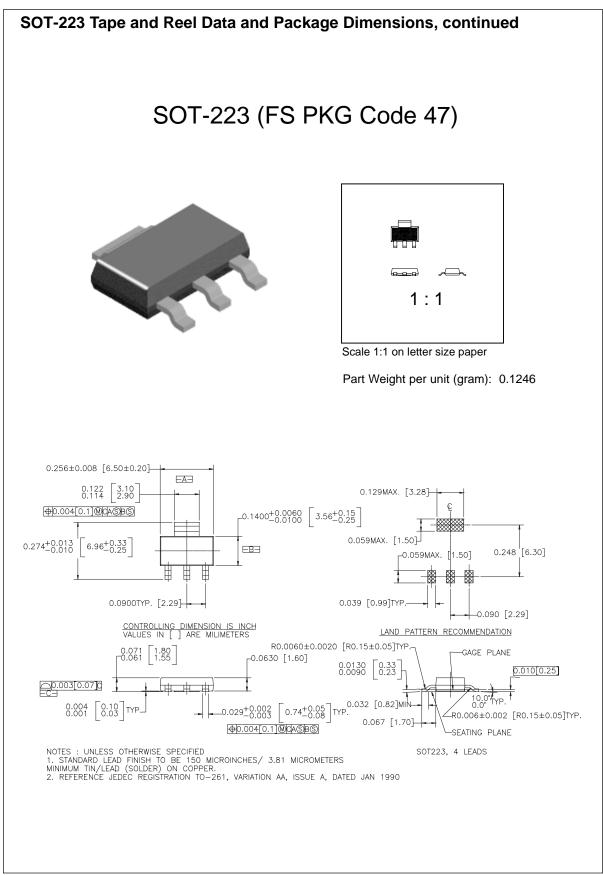
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reakdown Voltage Temp. Coefficient ero Gate Voltage Drain Current Gate - Body Leakage, Forward Gate - Body Leakage, Reverse ERISTICS (Note 2) Gate Threshold Voltage Gate Threshold Voltage Temp. Coefficient tatic Drain-Source On-Resistance On-State Drain Current corward Transconductance RACTERISTICS uput Capacitance Dutput Capacitance teverse Transfer Capacitance	$\begin{split} I_{D} &= 250 \ \mu\text{A}, \mbox{Referenced} \\ V_{DS} &= 60 \ V, \ V_{GS} &= 0 \ V \\ V_{GS} &= 20 \ V, \ V_{DS} &= 0 \ V \\ V_{GS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= $	T _J =125°C to 25 °C	1	1.6 -4 0.07 0.125 0.103 7 345 110	50 100 -100 2 0.1 0.18	mV ^ρ C μA μA nA nA MV ^ρ C Ω MV ^ρ C Ω A S pF pF
ero Gate Voltage Drain Current Gate - Body Leakage, Forward Gate - Body Leakage, Reverse ERISTICS (Note 2) Gate Threshold Voltage Gate Threshold Voltage Temp. Coefficient tatic Drain-Source On-Resistance On-State Drain Current forward Transconductance RACTERISTICS oput Capacitance Dutput Capacitance teverse Transfer Capacitance	$\begin{split} I_{D} &= 250 \ \mu\text{A}, \mbox{Referenced} \\ V_{DS} &= 60 \ V, \ V_{GS} &= 0 \ V \\ V_{GS} &= 20 \ V, \ V_{DS} &= 0 \ V \\ V_{GS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= 0 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= -20 \ V, \ V_{DS} &= -20 \ V \\ \hline V_{DS} &= $	T _J =125°C to 25 °C		1.6 -4 0.07 0.125 0.103 7 345 110	50 100 -100 2 0.1 0.18	μΑ μΑ nA nA WV/PC Ω Δ Α S PF
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ate - Body Leakage, Forward ate - Body Leakage, Reverse ERISTICS (Note 2) Bate Threshold Voltage Bate Threshold Voltage Temp. Coefficient tatic Drain-Source On-Resistance On-State Drain Current forward Transconductance RACTERISTICS nput Capacitance Dutput Capacitance Dutput Capacitance Dutput Capacitance Dutput Capacitance	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DS} = V_{GS}, I_D = 250 \text{ µA}$ $I_D = 250 \text{ µA}, \text{ Referenced}$ $V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 3.7 \text{ A}$ $V_{GS} = 5 \text{ V}, D_S = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, I_D = 4 \text{ A}$	to 25 °C		-4 0.07 0.125 0.103 7 345 110	100 -100 2 0.1 0.18	μΑ nA nA N M M P A S P F P F
Cate - Body Leakage, Reverse ERISTICS (Note 2) Cate Threshold Voltage Cate Threshold Voltage Temp. Coefficient Cate Threshold Voltage Temp. Coefficient	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DS} = V_{GS}, I_D = 250 \text{ µA}$ $I_D = 250 \text{ µA}, \text{ Referenced}$ $V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 3.7 \text{ A}$ $V_{GS} = 5 \text{ V}, D_S = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, I_D = 4 \text{ A}$	to 25 °C		-4 0.07 0.125 0.103 7 345 110	-100 2 0.1 0.18	nA nA wV/2C Ω A S pF
Cate - Body Leakage, Reverse ERISTICS (Note 2) Cate Threshold Voltage Cate Threshold Voltage Temp. Coefficient Cate Threshold Voltage Temp. Coefficient	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{DS} = V_{GS}, I_D = 250 \text{ µA}$ $I_D = 250 \text{ µA}, \text{ Referenced}$ $V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 3.7 \text{ A}$ $V_{GS} = 5 \text{ V}, D_S = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, I_D = 4 \text{ A}$			-4 0.07 0.125 0.103 7 345 110	2 0.1 0.18	V mV /²C Ω A S pF
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Cate Threshold Voltage Temp. Coefficient tatic Drain-Source On-Resistance On-State Drain Current orward Transconductance RACTERISTICS nput Capacitance Dutput Capacitance teverse Transfer Capacitance	$I_{D} = 250 \ \mu\text{A}, \text{Referenced}$ $V_{GS} = 10 \ \text{V}, \ I_{D} = 4 \ \text{A}$ $V_{GS} = 4.5 \ \text{V}, \ I_{D} = 3.7 \ \text{A}$ $V_{GS} = 5 \ \text{V}, \ V_{DS} = 10 \ \text{V}$ $V_{DS} = 5 \ \text{V}, \ I_{D} = 4 \ \text{A}$		10	0.07 0.125 0.103 7 345 110	0.18	Ω A S pF pF
An-State Drain-Source On-Resistance On-State Drain Current Fransconductance RACTERISTICS Aput Capacitance Dutput Capacitance Reverse Transfer Capacitance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3.7 \text{ A}$ $V_{GS} = 5 \text{ V}, \text{ I}_{D} = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, \text{ I}_{D} = 4 \text{ A}$		10	0.125 0.103 7 345 110	0.18	Ω A S pF pF
On-State Drain Current orward Transconductance RACTERISTICS nput Capacitance Output Capacitance	$V_{GS} = 4.5 \text{ V}, \ I_D = 3.7 \text{ A}$ $V_{GS} = 5 \text{ , } V_{DS} = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, \ I_D = 4 \text{ A}$	T _J =125°C	10	0.125 0.103 7 345 110	0.18	A S pF pF
iorward Transconductance RACTERISTICS uput Capacitance Dutput Capacitance leverse Transfer Capacitance	$V_{GS} = 5$, $V_{DS} = 10$ V $V_{DS} = 5$ V, $I_D = 4$ A		10	0.103 7 345 110		S pF pF
iorward Transconductance RACTERISTICS uput Capacitance Dutput Capacitance leverse Transfer Capacitance	$V_{GS} = 5$, $V_{DS} = 10$ V $V_{DS} = 5$ V, $I_D = 4$ A		10	7 345 110		S pF pF
iorward Transconductance RACTERISTICS uput Capacitance Dutput Capacitance leverse Transfer Capacitance	$V_{DS} = 5 V, I_{D} = 4 A$			345 110		S pF pF
RACTERISTICS nput Capacitance Dutput Capacitance leverse Transfer Capacitance				345 110		pF pF
nput Capacitance Dutput Capacitance leverse Transfer Capacitance	$V_{DS} = 25, V_{GS} = 0 V,$ f = 1.0 MHz			110		pF
Dutput Capacitance Reverse Transfer Capacitance	f = 1.0 MHz			110		pF
everse Transfer Capacitance				_		
						P
urn - On Delay Time	$V_{DD} = 25, I_{D} = 1 A,$			5	20	ns
urn - On Rise Time		$V_{\text{OD}} = 20, r_{\text{D}} = 170, r_{\text{C}} = 10 \text{V}, \text{R}_{\text{GEN}} = 6 \Omega$		7.5	20	ns
						ns
						ns
	$V_{DS} = 40 V, I_D = 4 A,$ $V_{GS} = 10 V$					nC
-					20	nC
5						nC
				J.Z		no
					25	А
				0.0		V
	•		Inting surfac			ns. R _{euc} is
a. 42°C/W when mounted on a 1 in ² pad of 2oz Cu.		d on a 0.066 in ²				on a 0.0012
	aximum Continuous Drain-Source Diode For ain-Source Diode Forward Voltage e junction-to-case and case-to-ambient thermal resistance when n while R _{gcA} is determined by the user's board design.	Im - Off Fall Time V _{DS} = 40 V, I _D = 4 A, V _{GS} = 10 V Intal Gate Charge V _{DS} = 10 V Intal Gate Charge V _{SS} = 10 V Intal Charge V _{SS} = 0 V, I _S = 2.5 A (Not structure) Intal Continuous Drain-Source Diode Forward Current Intal Continuous Drain-Source Diode Forward Current Intal Source Diode Forward Voltage V _{GS} = 0 V, I _S = 2.5 A (Not structure) Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is grapher Intel R _{gcx} is determined by the user's board design. Intel R _{gcx} is determined by the user's board design.	Im - Off Fall Time V _{DS} = 40 V, I _D = 4 A, V _{GS} = 10 V Intal Gate Charge V _{DS} = 40 V, I _D = 4 A, V _{GS} = 10 V Intal Gate Charge V _{DS} = 10 V Intal Charge V _{DS} = 10 V Intal Charge V _{DS} = 10 V Intal Charge V _{DS} = 0 V, I _D = 4 A, V _{GS} = 10 V Intal Charge V _{DS} = 10 V Intal Charge V _{DS} = 0 V, I _S = 2.5 A (Note 2) Intal Continuous Drain-Source Diode Forward Current V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{GS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 0 V, I _S = 2.5 A (Note 2) Interview V _{DS} = 0 V, I _S = 0 V,	Im - Off Fall Time V _{DS} = 40 V, I _D = 4 A, Ital Gate Charge V _{DS} = 10 V Ital Gate Charge V _{DS} = 10 V Ital Charge V _{DS} = 10 V Ital Charge V _{DS} = 0 V, I _D = 4 A, Ital Charge V _{DS} = 10 V Ital Charge V _{DS} = 0 V, I _D = 4 A, Ital Charge V _{DS} = 10 V Ital Charge V _{DS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 2.5 A (Note 2) Ital Charge V _{GS} = 0 V, I _S = 0	Im - Off Fall Time 7 trail Gate Charge $V_{DS} = 40 \text{ V}, \text{ I}_{D} = 4 \text{ A}, V_{GS} = 10 \text{ V}$ 13 ate-Source Charge 1.7 3.2 ate-Drain Charge 3.2 1.7 Second Charge 3.2 3.2 EDIODE CHARACTERISTICS AND MAXIMUM RATINGS 3.2 eximum Continuous Drain-Source Diode Forward Current 1.7 ain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, \text{ I}_{S} = 2.5 \text{ A} \pmod{20}$ 0.8 e junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of n while R_{gcA} is determined by the user's board design. b. 95'CW when mounted on a 0.066 in ² $\overset{\square}{=}$ c. 110'C/W when in ² pad of 2oz Cu. size paper size paper size paper b. 95'CW when mounted on a 0.066 in ² $\overset{\square}{=}$ c. 110'C/W when in ² pad of 2oz Cu.	Im - Off Fall Time 7 20 trail Gate Charge $V_{DS} = 40 \text{ V}, I_D = 4 \text{ A},$ 13 20 tate-Source Charge V _{GS} = 10 V 1.7 1.7 ate-Drain Charge 3.2 3.2 1.7 DIODE CHARACTERISTICS AND MAXIMUM RATINGS aximum Continuous Drain-Source Diode Forward Current 2.5 ain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 2.5 \text{ A} (Note 2)$ 0.8 1.2 e junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of n while R _{got} is determined by the user's board design. the drain pin n while R _{got} is determined by the user's board design. a. 42°CW when mounted on a 1 in² pad of 2oz Cu. $0.95°CW$ when mounted on a 0.066 in² \bigcirc \bigcirc c. 110°CW when mounted in² pad of 2oz Cu. size paper size paper b. 95°CW when mounted on a 0.066 in² \bigcirc \bigcirc \bigcirc \bigcirc











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Datasheet Identification	Product Status	Definition
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